



# STD9NM60N - STD9NM60N-1 STP9NM60N - STF9NM60N

N-CHANNEL 600V - 0.51Ω - 9A - TO220/TO-220FP/DPAK/IPAK  
SECOND GENERATION MDmesh™ MOSFET

Target Specification

## General features

Type	V <sub>DSS</sub> (@T <sub>jmax</sub> )	R <sub>DS(on)</sub>	I <sub>D</sub>
STD9NM60N	650 V	<0.56 Ω	9 A
STD9NM60N-1	650 V	<0.56 Ω	9 A
STF9NM60N	650 V	<0.56 Ω	9 A <i>Note 3</i>
STP9NM60N	650 V	<0.56 Ω	9 A

- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE

## Description

The STP9NM60N is realized with the second generation of MDmesh Technology. This revolutionary MOSFET associates a new vertical structure to the Company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

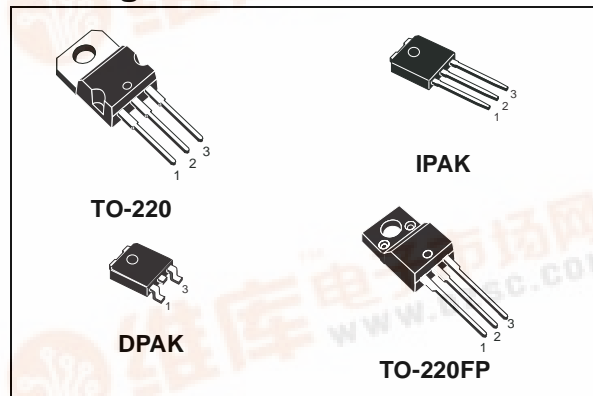
## Applications

- HIGHER EFFICIENCIES

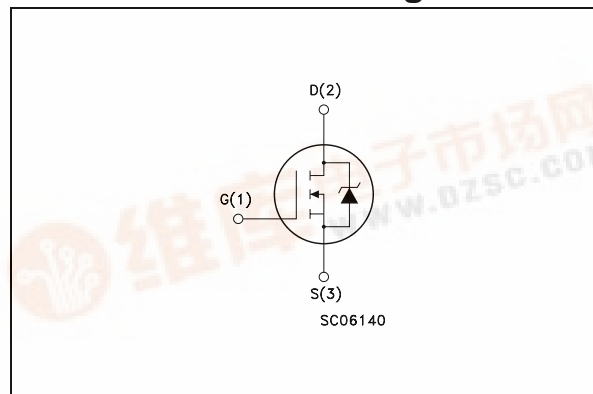
## Order codes

Sales Type	Marking	Package	Packaging
STD9NM60N-1	D9NM60N-1	DPAK	TAPE & REEL
STD9NM60N	D9NM60N	IPAK	TUBE
STF9NM60N	P9NM60N	TO-220	TUBE
STF9NM60N	F9NM60N	TO-220FP	TUBE

## Package



## Internal schematic diagram



# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220/DPAK/IPAK	TO-220FP	
$V_{DS}$	Drain-source Voltage ( $V_{GS}=0$ )	600		V
$V_{DGR}$	Drain-gate Voltage ( $R_{GS}=20k\Omega$ )	600		V
$V_{GS}$	Gate-Source Voltage	$\pm 25$		V
$I_D$	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	9	9 ( <i>Note 3</i> )	A
$I_D$	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	6	6 ( <i>Note 3</i> )	A
$I_{DM}$ <i>Note 2</i>	Drain Current (pulsed)	35	35 ( <i>Note 3</i> )	A
$P_{TOT}$	Total Dissipation at $T_C = 25^\circ\text{C}$	100	25	W
	Derating Factor	0.8	0.2	W/°C
dv/dt <i>Note 1</i>	Peak Diode Recovery voltage slope	TBD		V/ns
$V_{ISO}$	Insulation Withstand Voltage (DC)	--	2500	V
$T_j$ $T_{stg}$	Operating Junction Temperature Storage Temperature	-55 to 150		°C

**Table 2. Thermal data**

		TO-220	DPAK/IPAK	TO-220FP	Unit
Rthj-case	Thermal Resistance Junction-case Max	1.25		5	°C/W
Rthj-amb	Thermal Resistance Junction-amb Max	62.5	100	62.5	°C/W
$T_l$	Maximum Lead Temperature For Soldering Purpose	300			°C

**Table 3. Avalanche characteristics**

Symbol	Parameter	Max Value	Unit
$I_{AS}$	Avalanche Current, repetitive or Not-Repetitive (pulse width limited by $T_j$ max)	TBD	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j=25^\circ\text{C}$ , $I_D=I_{AS}$ , $V_{DD}=50\text{V}$ )	TBD	mJ

## 2 Electrical characteristics

(T<sub>CASE</sub> = 25 °C unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	600			V
dv/dt <i>Note 4</i>	Drain-Source Voltage Slope	V <sub>dd</sub> =TBD, I <sub>d</sub> =TBD, V <sub>gs</sub> =TBD	TBD			V/ns
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating, V <sub>DS</sub> = Max Rating, T <sub>c</sub> = 125°C			1 10	μA μA
I <sub>GSS</sub>	Gate Body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±25V			±100	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A		0.51	0.56	Ω

**Table 5. Dynamic**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> <i>Note 5</i>	Forward Transconductance	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4.5 A I <sub>D</sub> = 10A		5		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		880 205 26		pF pF pF
C <sub>oss eq.</sub> <i>Note 6</i>	Equivalent Output Capacitance	V <sub>GS</sub> = 0, V <sub>DS</sub> = 0V to 480V		TBD		pF
R <sub>g</sub>	Gate Input Resistance	f = 1MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.6		Ω
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V <sub>DD</sub> = 480V, I <sub>D</sub> = 4.5A V <sub>GS</sub> = 10V (see Figure 2)		32 TBD TBD		nC nC nC

**Table 6. Switching times**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD}=300\text{ V}$ , $I_D=4.5\text{ A}$ , $R_G=4.7\Omega$ , $V_{GS}=10\text{ V}$ (see Figure 3)		TBD TBD		ns ns
$t_{d(off)}$ $t_f$	Off voltage Rise Time FallTime	$V_{DD}=300\text{ V}$ , $I_D=4.5\text{ A}$ , $R_G=4.7\Omega$ , $V_{GS}=10\text{ V}$ (see Figure 3)		TBD TBD		
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD}=480\text{ V}$ , $I_D=4.5\text{ A}$ , $R_G=4.7\Omega$ , $V_{GS}=10\text{ V}$ (see Figure 3)		TBD TBD TBD		ns ns ns

**Table 7. Source drain diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}$	Source-drain Current Source-drain Current (pulsed)				9 35	A A
$V_{SD}$ <i>Note 5</i>	Forward on Voltage	$I_{SD}=9\text{ A}$ , $V_{GS}=0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD}=9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=100\text{ V}$ , $T_j=25^\circ\text{C}$		TBD TBD TBD		ns $\mu\text{C}$ A
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD}=9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=100\text{ V}$ , $T_j=150^\circ\text{C}$		TBD TBD TBD		ns $\mu\text{C}$ A

(1)  $I_{SD} \leq 9\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$

(2) Pulse width limited by safe operating area

(3) Limited only by maximum temperature allowed

(4) Characteristics value at turn off on inductive load

(5) Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

(6)  $C_{oss,eq}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

### 3 Test circuits

Figure 1. Switching Times Test Circuit For Resistive Load

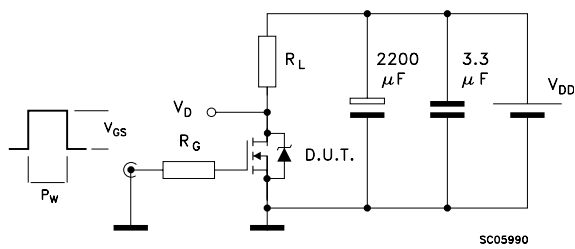


Figure 2. Gate Charge Test Circuit

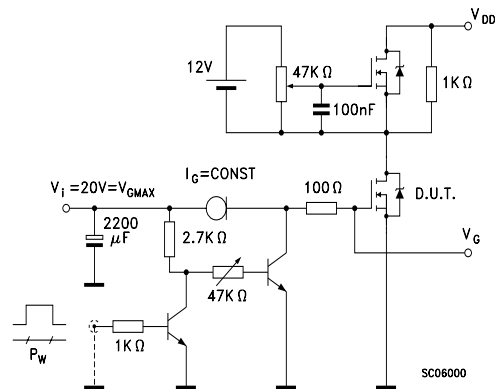


Figure 3. Test Circuit For Inductive Load Switching and Diode Recovery Times

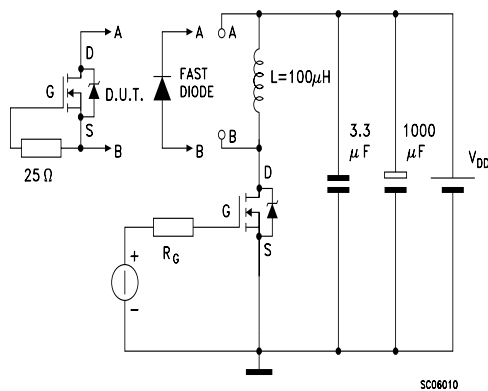


Figure 5. Unclamped Inductive Load Test Circuit

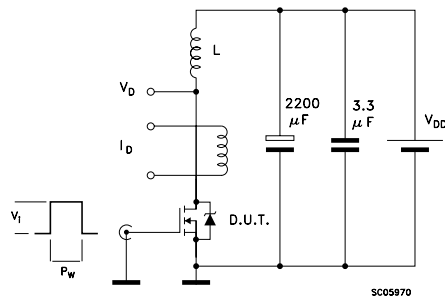
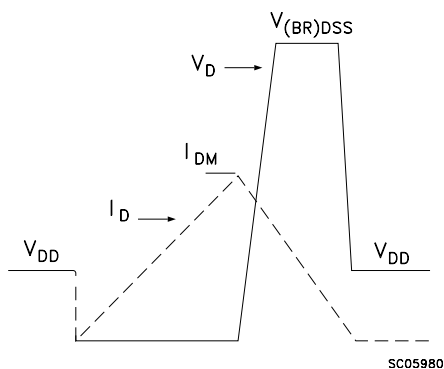


Figure 4. Unclamped Inductive Waveform

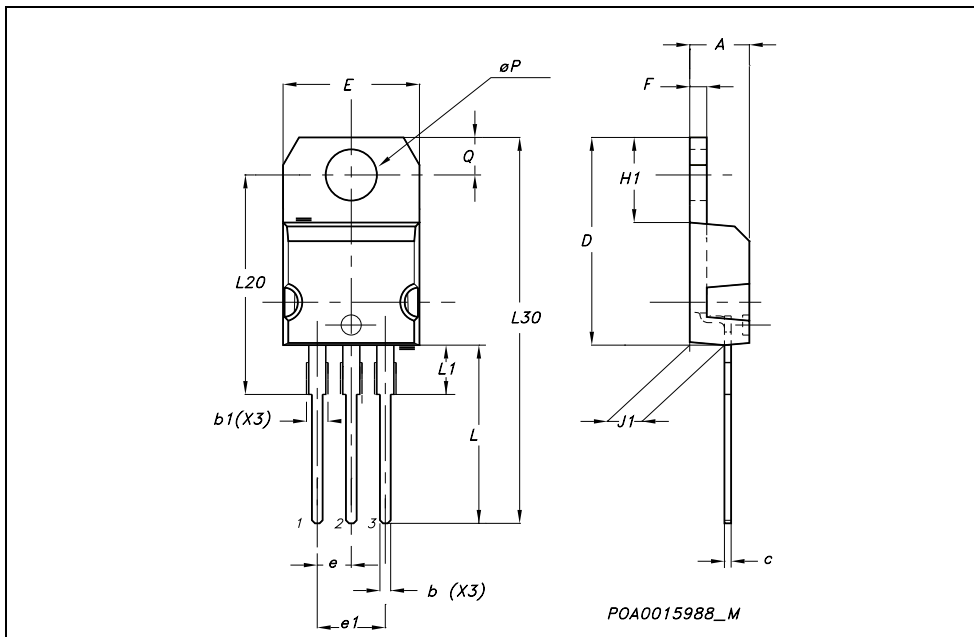


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

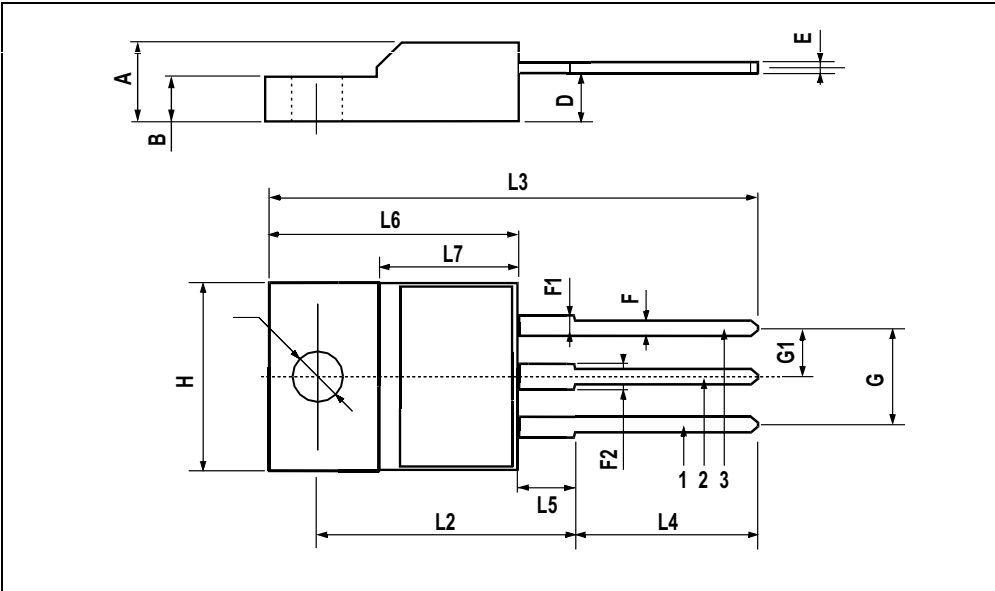
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



**TO-220FP MECHANICAL DATA**

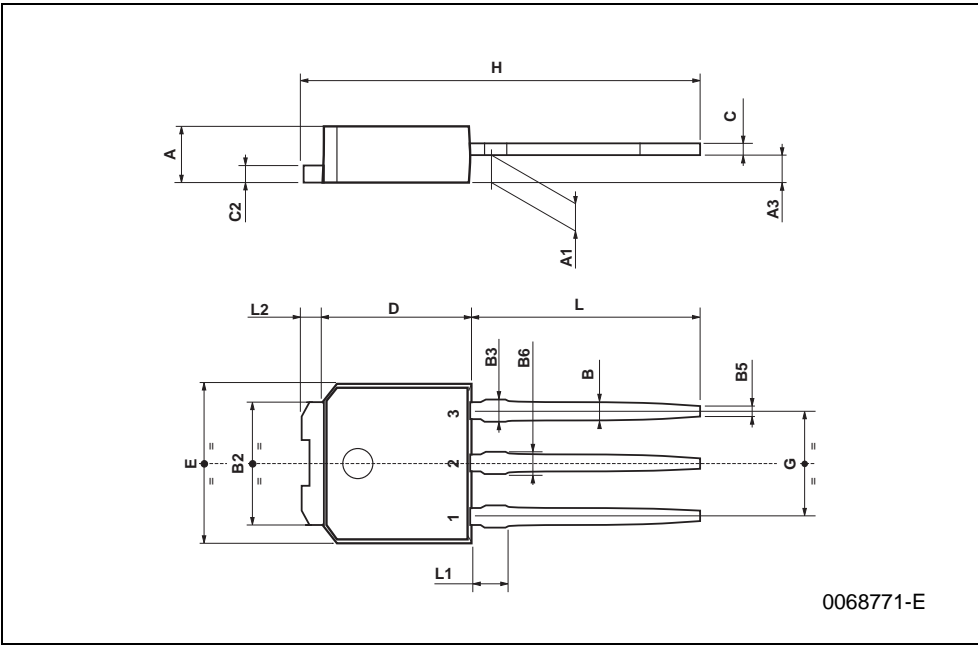
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126





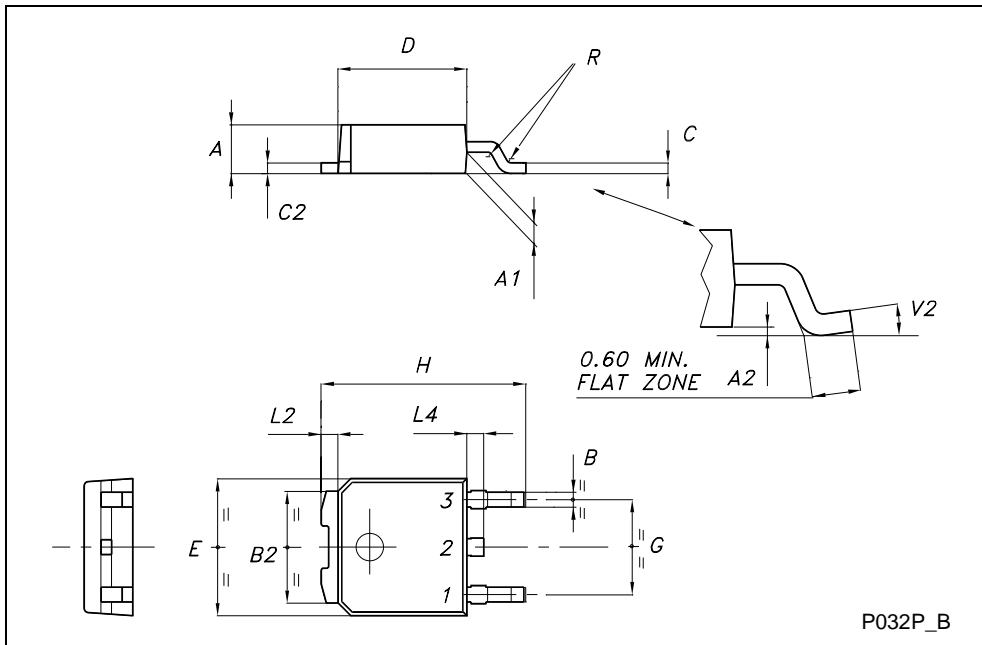
**TO-251 (IPAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



**TO-252 (DPAK) MECHANICAL DATA**

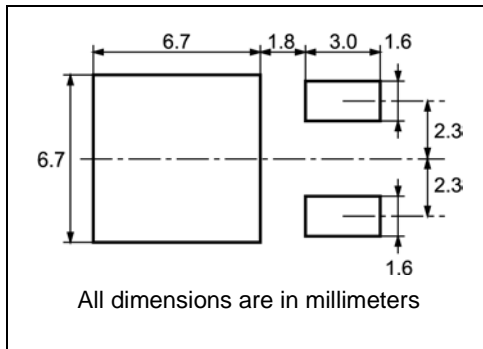
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



P032P\_B

## 5 Packing mechanical data

### DPAK FOOTPRINT



### TAPE AND REEL SHIPMENT

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

## 6 Revision History

Date	Revision	Changes
05-Oct-2005	1	First release

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